





# YJL3400A

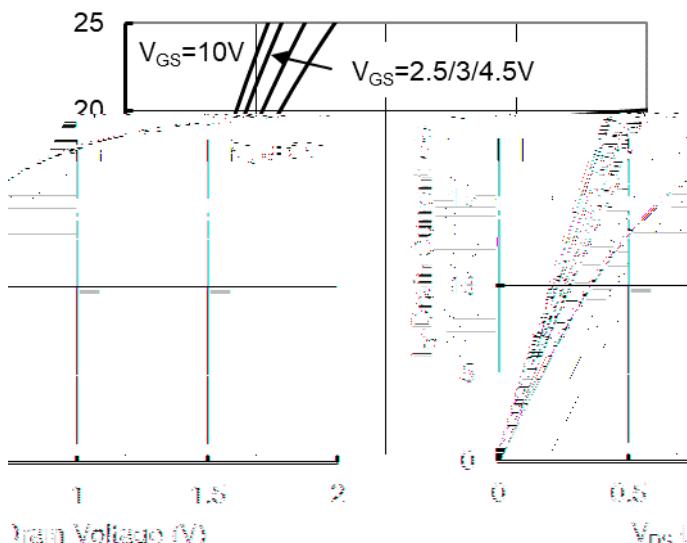
## Electrical Characteristics ( $T_J=25^\circ\text{C}$ unless otherwise noted)

| Parameter                         | Symbol                   | Conditions  | Min  | Typ   | Max | Units |
|-----------------------------------|--------------------------|---|------|-------|-----|-------|
| <b>Static Parameter</b>           |                          |   |      |       |     |       |
| Drain-Source Breakdown Voltage    | $\text{BV}_{\text{DSS}}$ | $V_{\text{GS}}=0\text{V}, I_{\text{D}}=250$   | 30   |       |     | V     |
| Zero Gate Voltage Drain Current   | $I_{\text{DSS}}$         | $V_{\text{DS}}=30\text{V}, V_{\text{GS}}=0\text{V}$   |      |       | 1   |       |
| Gate-Body Leakage Current         | $I_{\text{GSS1}}$        | $V_{\text{GS}}=12\text{V}, V_{\text{DS}}=0\text{V}$   |      |       | 100 | nA    |
| Gate Threshold Voltage            | $V_{\text{GS(th)}}$      | $V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250$   | 0.65 | 0.9   | 1.5 | V     |
| Static Drain-Source On-Resistance | $R_{\text{DS(ON)}}$      | $V_{\text{GS}}=10\text{V}, I_{\text{D}}=5.6\text{A}$  |      | 20    | 25  | m     |
|                                   |                          | $V_{\text{GS}}=4.5\text{V}, I_{\text{D}}=5\text{A}$   |      | 23    | 31  |       |
|                                   |                          | $V_{\text{GS}}=2.5\text{V}, I_{\text{D}}=3\text{A}$   |      | 27    | 45  |       |
| Diode Forward Voltage             | $V_{\text{SD}}$          | $I_{\text{S}}=5.6\text{A}, V_{\text{GS}}=0\text{V}$   |      |       | 1.2 | V     |
| <b>Dynamic Parameters</b>         |                          |   |      |       |     |       |
| Input Capacitance                 | $C_{\text{iss}}$         | $V_{\text{DS}}=15\text{V}, V_{\text{GS}}=0\text{V}, f=1\text{MHz}$                                  |      | 630   |     | pF    |
| Output Capacitance                | $C_{\text{oss}}$         |   |      | 55    |     |       |
| Reverse Transfer Capacitance      | $C_{\text{rss}}$         |   |      | 71    |     |       |
| <b>Switching Parameters</b>       |                          |   |      |       |     |       |
| Total Gate Charge                 | $Q_g$                    | $V_{\text{GS}}=10\text{V}, V_{\text{DS}}=15\text{V}, I_{\text{D}}=5.6\text{A}$                      |      | 17.25 |     | nC    |
| Gate-Source Charge                | $Q_{\text{gs}}$          |   |      | 2.1   |     |       |
| Gate-Drain Charge                 | $Q_{\text{gd}}$          |   |      | 2     |     |       |
| Reverse Recovery Charge           | $Q_{\text{rr}}$          | $I_{\text{F}}=5.6\text{A}, dI/dt=100\text{A/us}$  |      | 1.1   |     | ns    |
| Reverse Recovery Time             | $t_{\text{rr}}$          |   |      | 13.1  |     |       |
| Turn-on Delay Time                | $t_{\text{D(on)}}$       |   |      | 4.4   |     |       |
| Turn-on Rise Time                 | $t_r$                    | $V_{\text{GS}}=10\text{V}, V_{\text{DS}}=15\text{V}, I_{\text{D}}=5.6\text{A}$<br>$R_{\text{GEN}}=$ |      | 28.2  |     |       |
| Turn-off Delay Time               | $t_{\text{D(off)}}$      |   |      | 16.2  |     |       |
| Turn-off fall Time                | $t_f$                    |   |      | 26    |     |       |

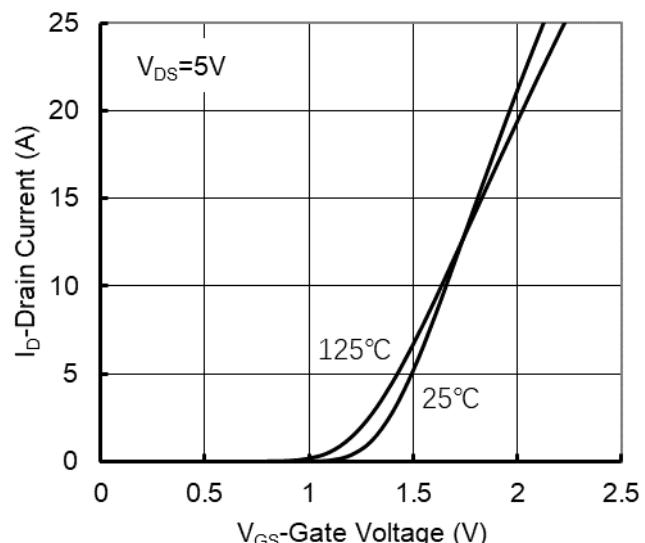
A. Pulse Test: Pulse Width 300us, Duty cycle 2%.

B.  $R_{\text{JA}}$  is the sum of the junction-to-case and case-to-ambient thermal resistance, where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\text{JC}}$  is guaranteed by design, while  $R_{\text{JA}}$  is determined by the board design. The maximum rating presented here is based on mounting on a 1 in 2 pad of 2oz copper.

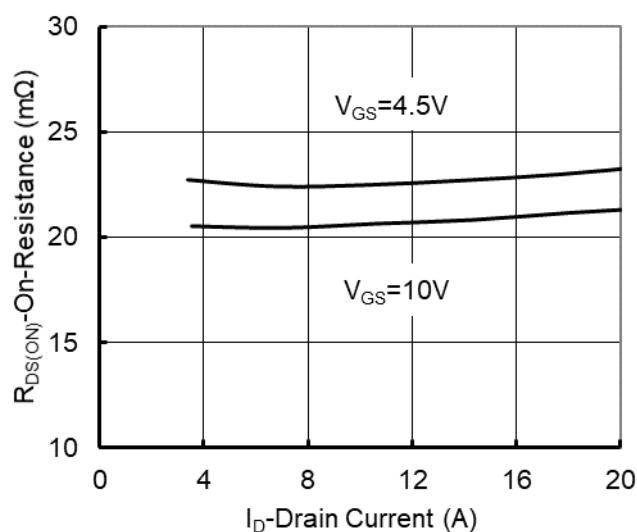
## ■ Typical Performance Characteristics



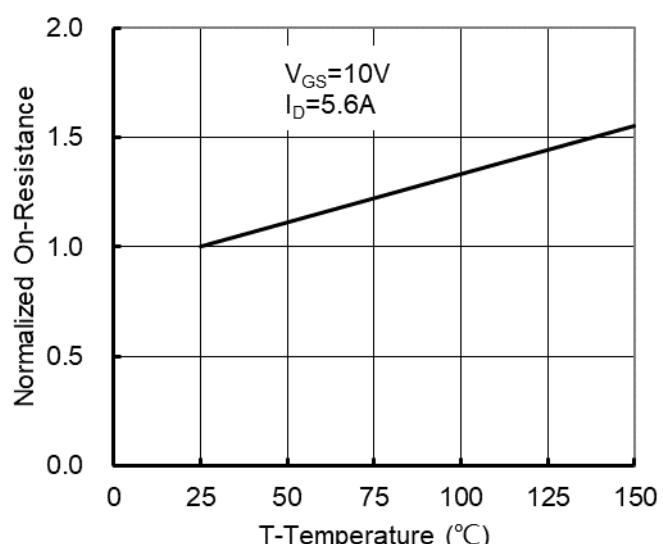
**Figure 1. Output Characteristics**



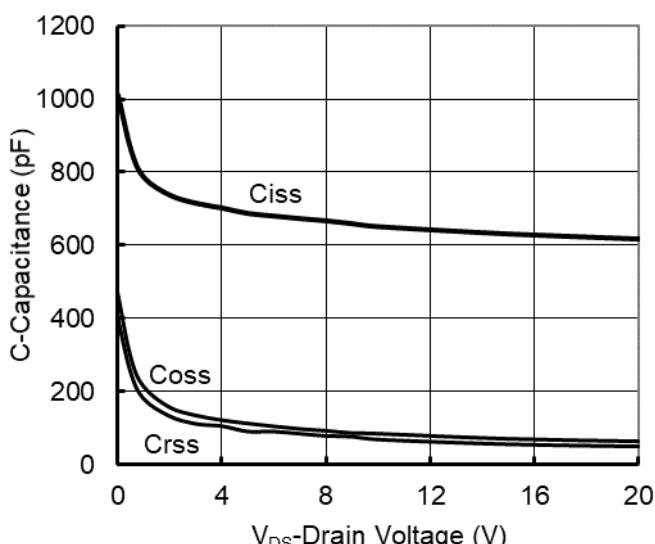
**Figure 2. Transfer Characteristics**



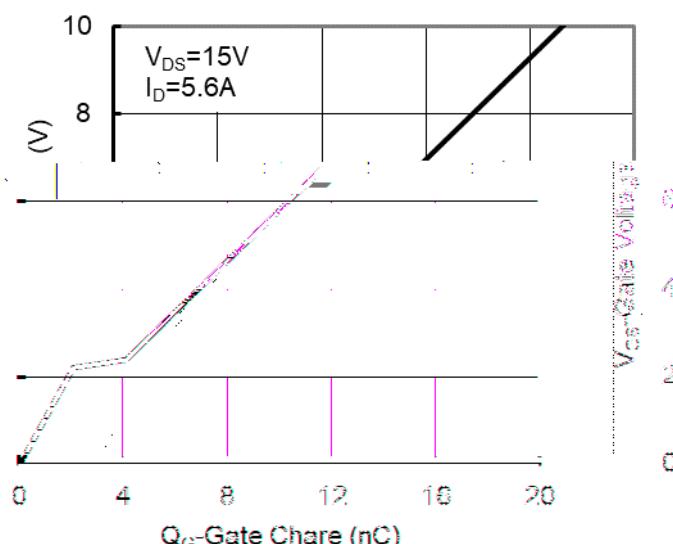
**Figure 3: On-Resistance vs. Drain Current and Gate Voltage**



**Figure 4: On-Resistance vs. Junction Temperature**



**Figure 5. Capacitance Characteristics**



**Figure 6. Gate Charge**



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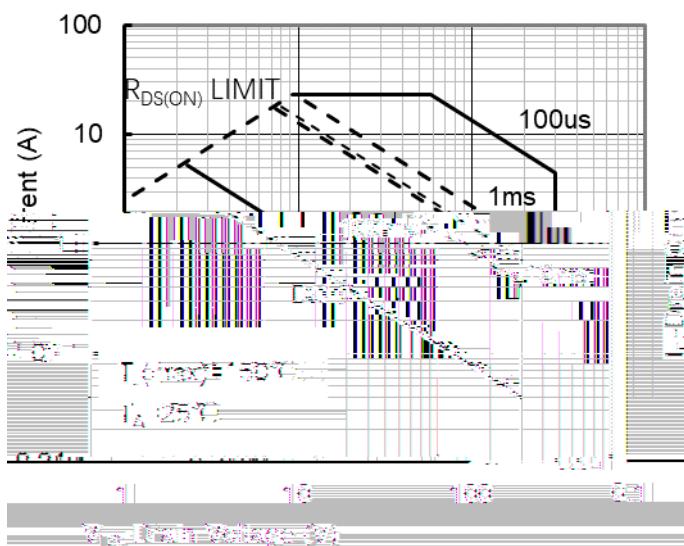


Figure 7. Safe Operation Area

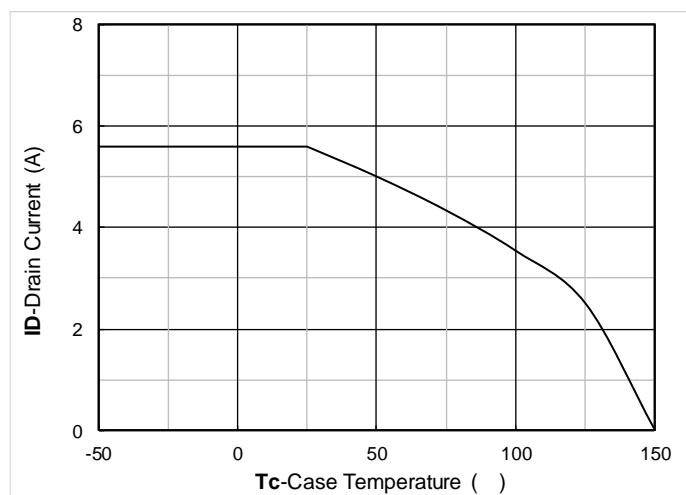


Figure 8. Current dissipation

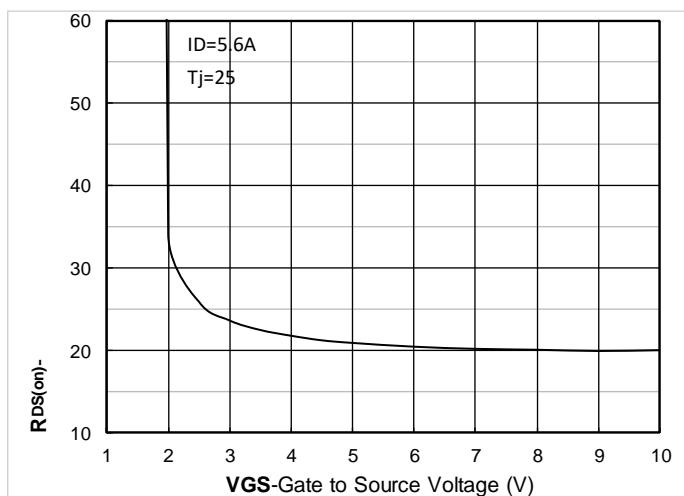


Figure 9. On-Resistance vs Gate to Source Voltage

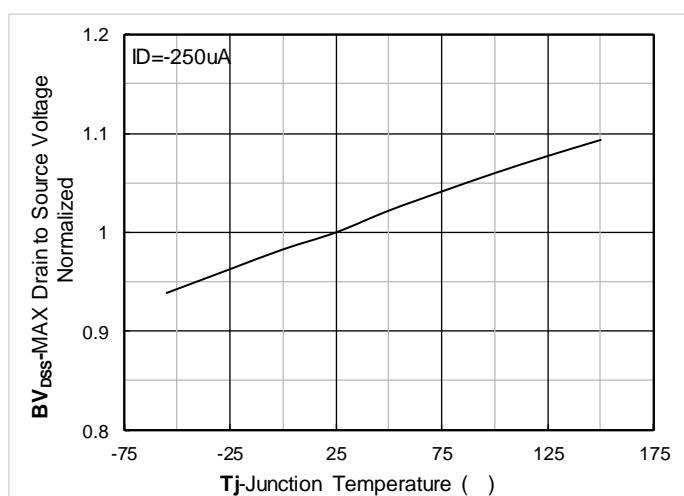
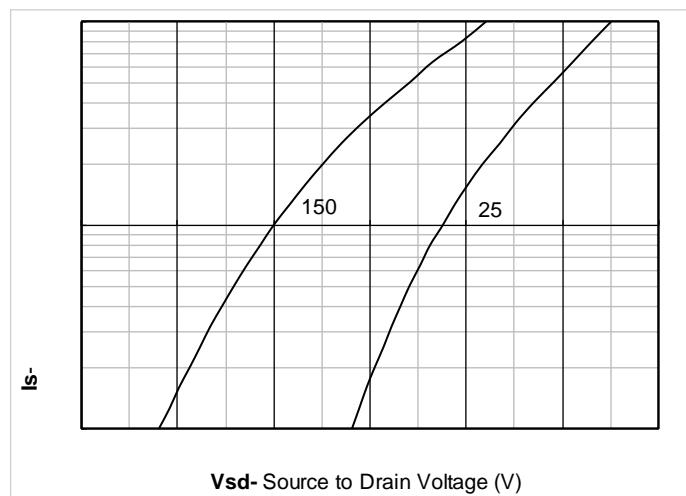


Figure 11. Normalized breakdown voltage



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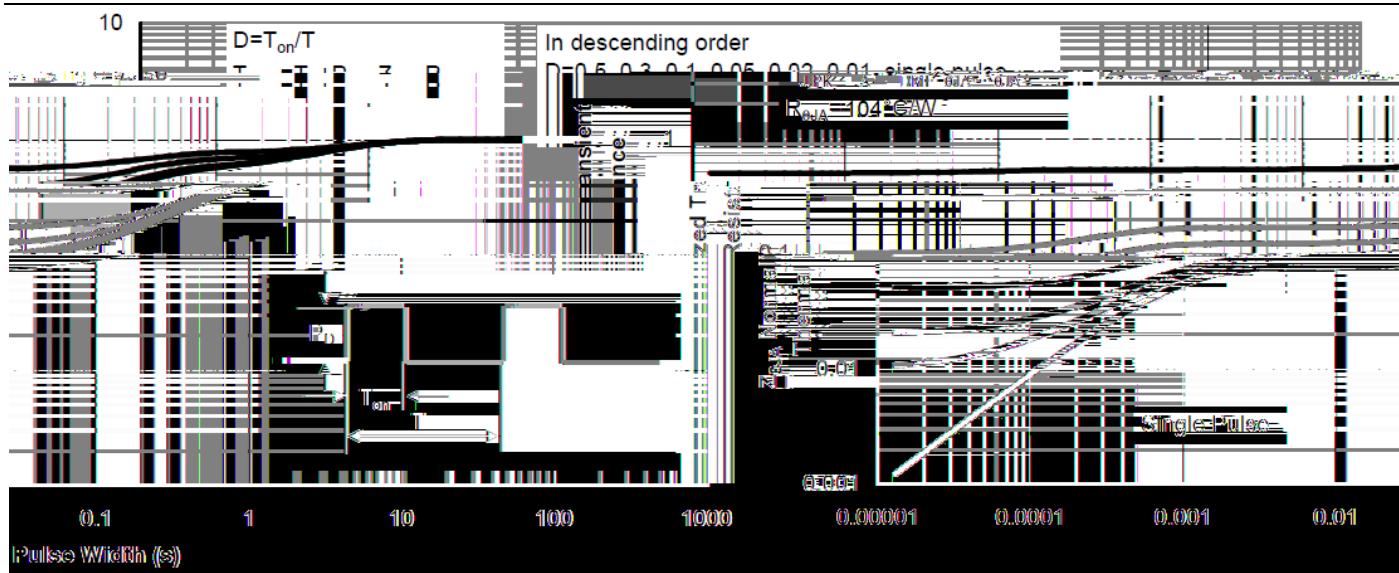
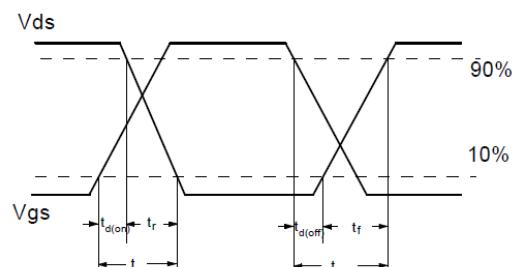
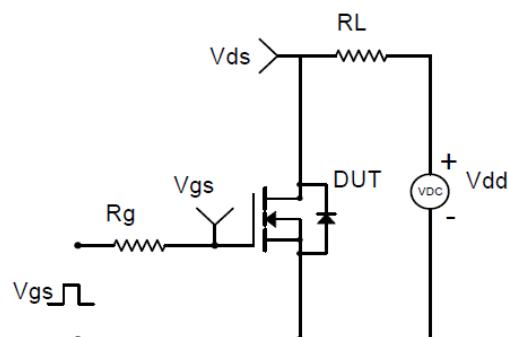


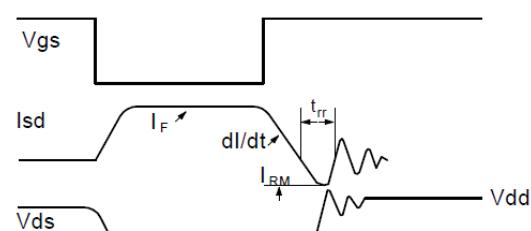
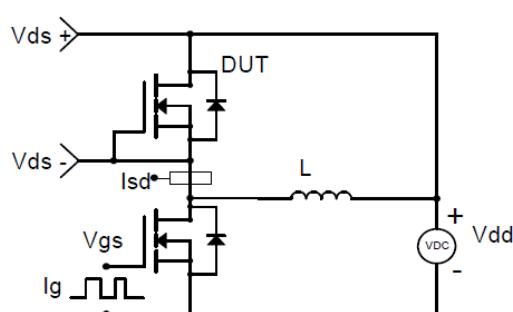
Figure13. Normalized Maximum Transient Thermal Impedance



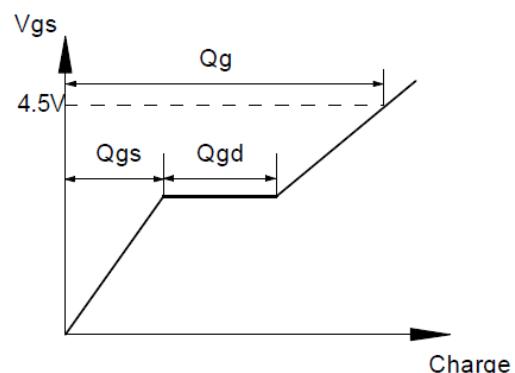
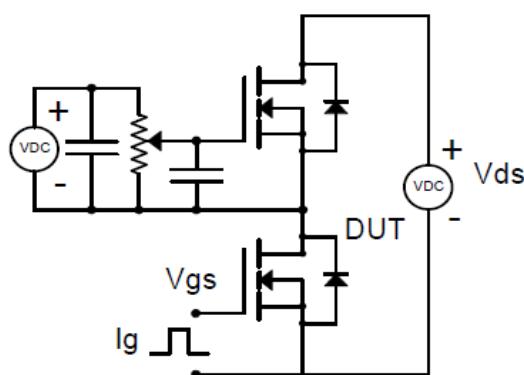
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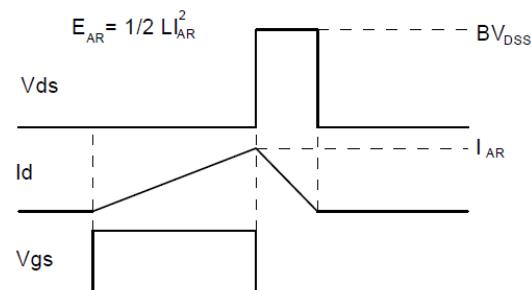
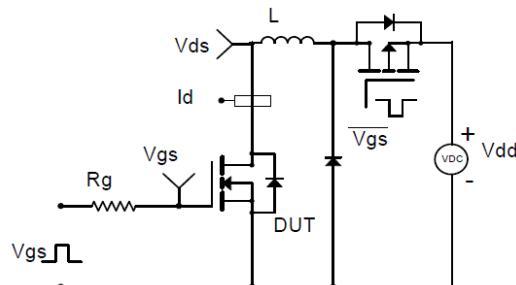
**Resistive Switching Test Circuit & Waveforms**



**Diode Recovery Test Circuit & Waveforms**



**Gate Charge Test Circuit & Waveform**



**Unclamped Inductive Switching (UIS) Test Circuit & Waveforms**



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## SOT-23 Package information



UNIT mm

### NOTE:

- 1.PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
- 2.TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
- 3.THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.



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